

**REMARKS**

No new matter has been introduced.

The wording in Claim 13 has been amended to avoid multiple dependency.

Early and favorable consideration with respect to this application is respectfully requested.

These changes have been made in accordance with 37 C.F.R. § 1.121 as amended on November 7, 2000. A marked-up version of Claim 13 indicating the changes is enclosed with this Preliminary Amendment.

Should any questions arise in connection with this application, the undersigned respectfully requests that he be contacted at the number indicated below.

Respectfully submitted,

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By:

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**Attachment to Preliminary Amendment dated December 6, 2001**

**Marked-up Claims**

13. (Amended) A semiconductor device accordin to claim 1 [or claim 4], comprising a SRAM cell, wherein the wiring layer is connected to the memory node of the SRAM cell.

1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 29 30 31 32 33 34 35 36 37 38 39 40 41 42 43 44 45 46 47 48 49 50 51 52 53 54 55 56 57 58 59 60 61 62 63 64 65 66 67 68 69 70 71 72 73 74 75 76 77 78 79 80 81 82 83 84 85 86 87 88 89 90 91 92 93 94 95 96 97 98 99 100